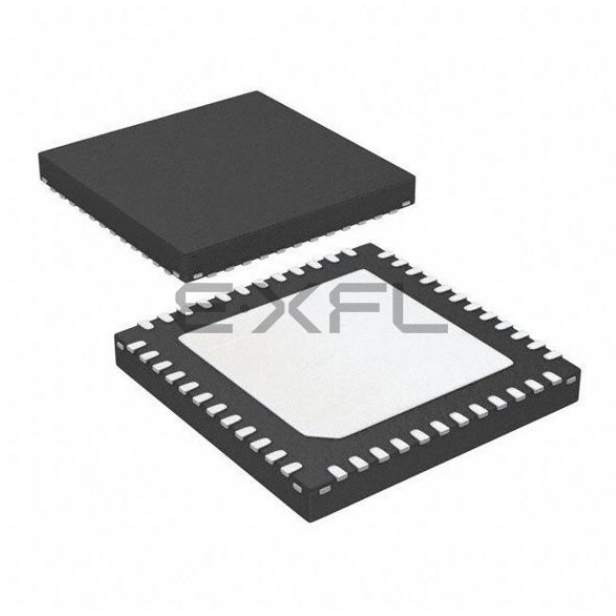
Renesas Electronics America Inc - R7FS124773A01CNE#AC0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	CANbus, I²C, SCI, SPI, UART/USART, USB
Peripherals	LVD, POR, PWM, WDT
Number of I/O	35
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 14x14b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-WFQFN Exposed Pad
Supplier Device Package	48-HWQFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r7fs124773a01cne-ac0

Ultra-low power 32-MHz Arm® Cortex®-M0+ microcontroller, 128-KB code flash memory, 16-KB SRAM, Capacitive Touch Sensing Unit, 14-bit A/D Converter, 12-bit D/A Converter, security and safety features.

Features

■ Arm Cortex-M0+ Core
- Armv6-M architecture
- Maximum operating frequency: 32 MHz
- Debug and Trace: DWT, BPU, CoreSight™ MTB-M0+
- CoreSight Debug Port: SW-DP

■ Memory
- 128-KB code flash memory
- 4-KB data flash memory (100,000 erase/write cycles)
- Up to 16-KB SRAM
- 128-bit unique ID

■ Connectivity
- USB 2.0 Full-Speed Module (USBFS)
  - On-chip transceiver with voltage regulator
  - Compliant with USB Battery Charging Specification 1.2
- Serial Communications Interface (SCI) × 3
  - UART
  - Simple IIC
  - Simple SPI
- Serial Peripheral Interface (SPI) × 2
- I^2C bus interface (IIC) × 2
- CAN module (CAN)

■ Analog
- 14-Bit A/D Converter (ADC14)
- 12-Bit D/A Converter (DAC12)
- Low-Power Analog Comparator (ACMPLP) × 2
- Temperature Sensor (TSN)

■ Timers
- General PWM Timer 32-Bit (GPT32)
- General PWM Timer 16-Bit (GPT16) × 6
- Asynchronous General-Purpose Timer (AGT) × 2
- Watchdog Timer (WDT)

■ Safety
- SRAM Parity Error Check
- Flash Area Protection
- ADC self-diagnosis function
- Clock Frequency Accuracy Measurement Circuit (CAC)
- Cyclic Redundancy Check (CRC) Calculator
- Data Operation Circuit (DOC)
- Port Output Enable for GPT (POEG)
- Independent Watchdog Timer (IWDT)
- GPIO Readback Level Detection
- Register Write Protection
- Main Oscillator Stop Detection

■ System and Power Management
- Low-power modes
- Realtime Clock (RTC)
- Event Link Controller (ELC)
- Data Transfer Controller (DTC)
- Key Interrupt Function (KINT)
- Power-on reset
- Low Voltage Detection with voltage settings

■ Security and Encryption
- AES128/256
- True Random Number Generator (TRNG)

■ Human Machine Interface (HMI)
- Capacitive Touch Sensing Unit (CTSU)

■ Multiple Clock Sources
- Main clock oscillator (MOSC)
  (1 to 20 MHz when VCC = 2.4 to 5.5 V)
  (1 to 8 MHz when VCC = 1.8 to 5.5 V)
  (1 to 4 MHz when VCC = 1.6 to 5.5 V)
- Sub-clock oscillator (SOSC) (32.768 kHz)
- High-speed on-chip oscillator (HOCO)
  (24, 32, 48, 64 MHz when VCC = 2.4 to 5.5 V)
  (24, 32, 48 MHz when VCC = 1.8 to 5.5 V)
  (24, 32 MHz when VCC = 1.6 to 5.5 V)
- Middle-speed on-chip oscillator (MOCO) (8 MHz)
- Low-speed on-chip oscillator (LOCO) (32.768 kHz)
- Independent watchdog timer OCO (15 kHz)
- Clock trim function for HOCO/MOCO/LOCO
- Clock out support

■ General Purpose I/O Ports
- Up to 51 input/output pins
  - Up to 3 CMOS input
  - Up to 48 CMOS input/output
    - Up to 6 input/output 5 V tolerant
    - Up to 16 pins high current (20 mA)

■ Operating Voltage
- VCC: 1.6 to 5.5 V

■ Operating Temperature and Packages
- Ta = –40°C to +85°C
  - 36-pin LGA (4 mm × 4 mm, 0.5 mm pitch)
- Ta = –40°C to +105°C
  - 64-pin LQFP (10 mm × 10 mm, 0.5 mm pitch)
  - 48-pin LQFP (7 mm × 7 mm, 0.5 mm pitch)
  - 64-pin QFN (8 mm × 8 mm, 0.4 mm pitch)
  - 48-pin QFN (7 mm × 7 mm, 0.5 mm pitch)
  - 40-pin QFN (6 mm × 6 mm, 0.5 mm pitch)

Table 1.11 Security

Feature	Functional description
AES	See section 38, AES Engine in User's Manual
True Random Number Generator (TRNG)	See section 39, True Random Number Generator (TRNG) in User's Manual

1.2 Block Diagram

Figure 1.1 shows the block diagram of the MCU superset. Individual devices within the group may have a subset of the features.

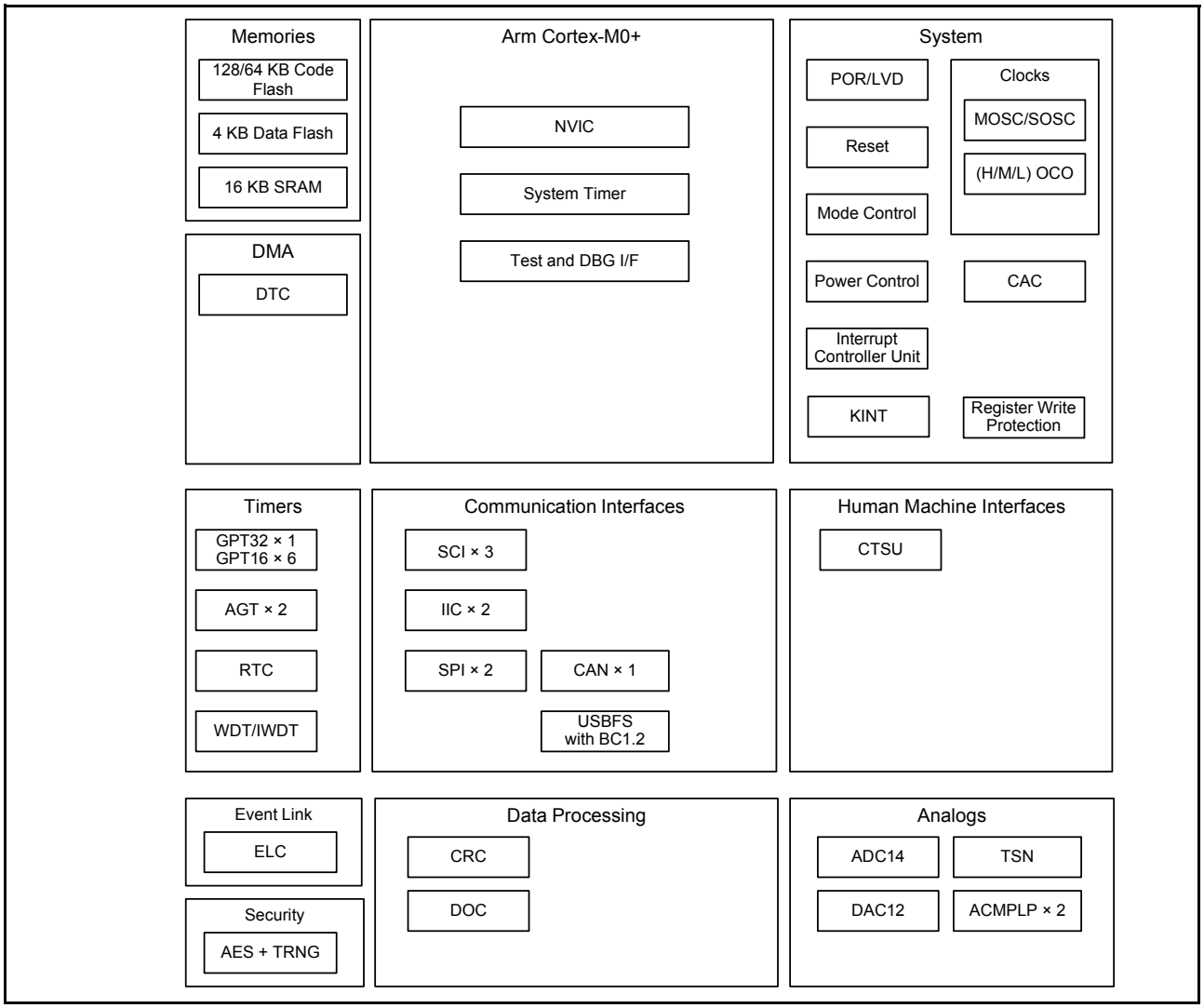


Figure 1.1 Block diagram

1.3 Part Numbering

Figure 1.2 shows how to read the product part number, memory capacity, and package types. Table 1.12 shows a list of products.

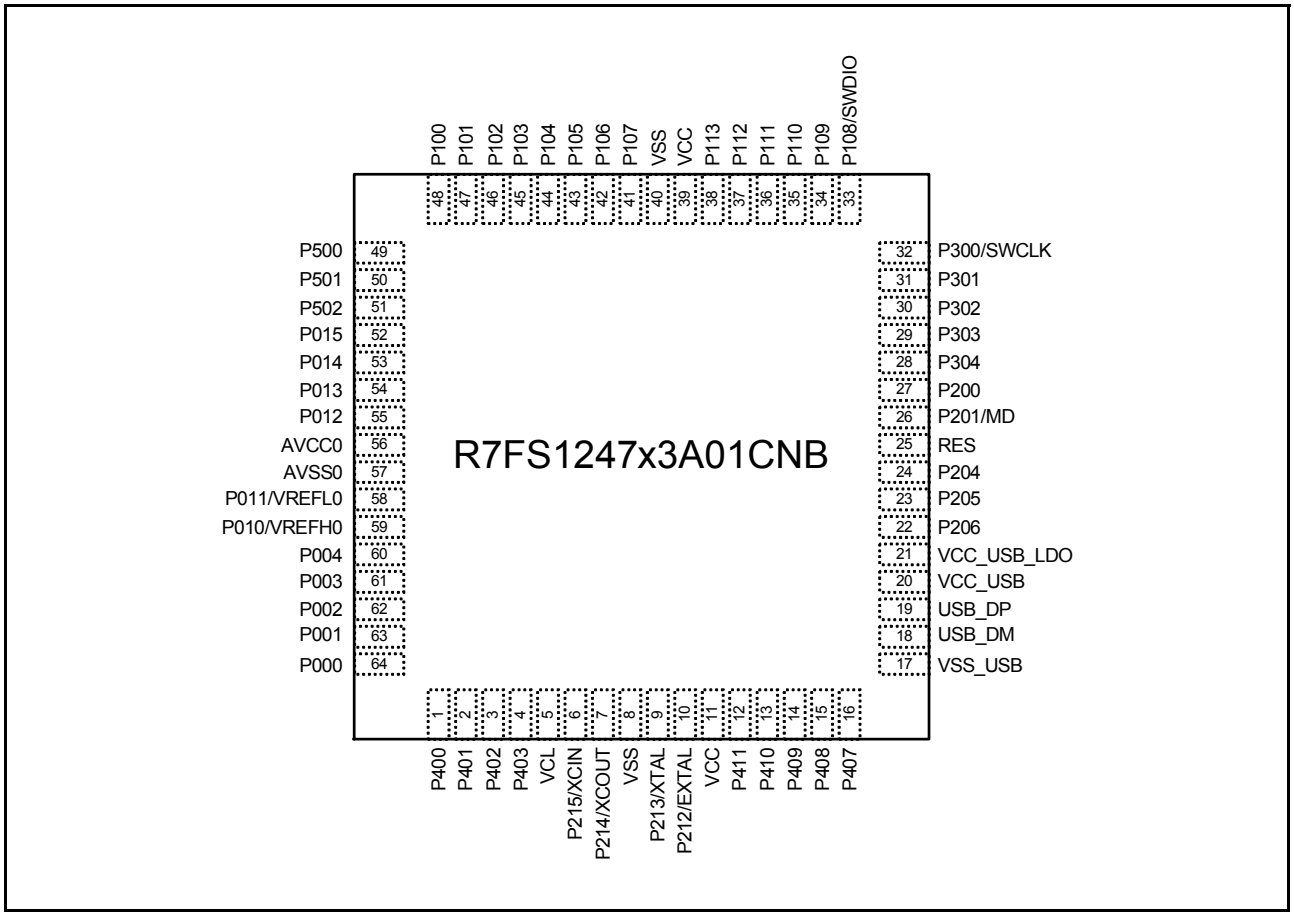


Figure 1.4 Pin assignment for QFN 64-pin (top view)

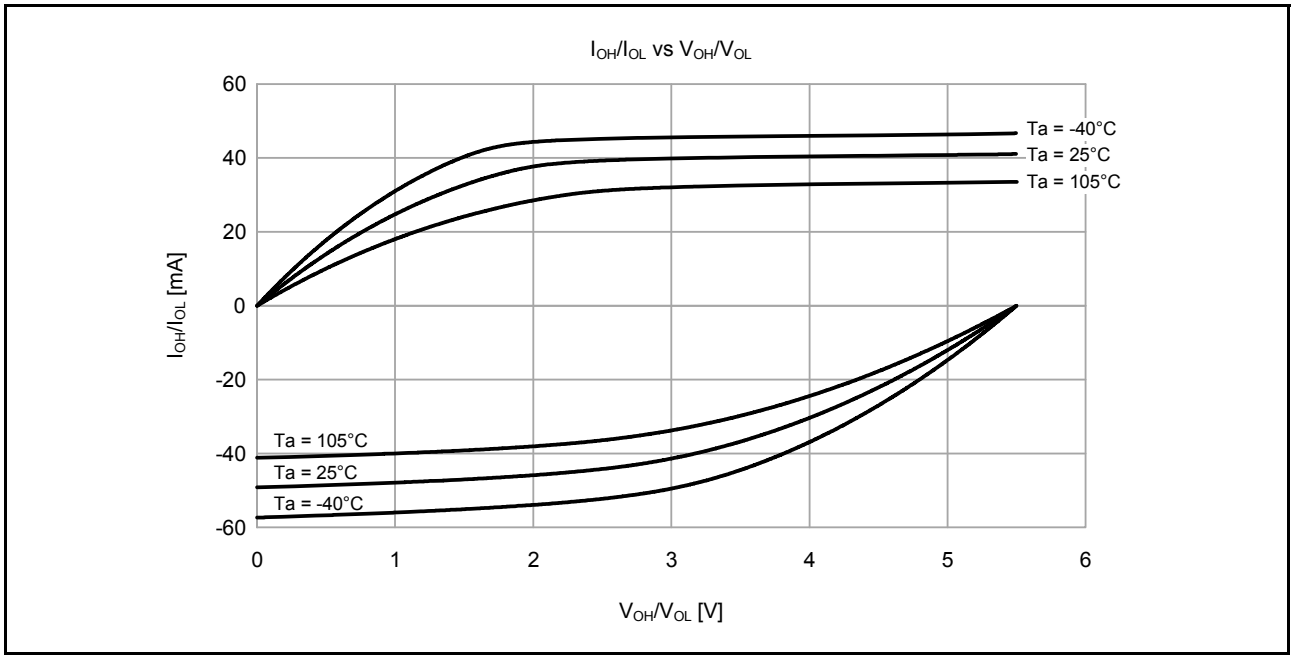


Figure 2.6 **V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 5.5 V when low drive output is selected (reference data)**

2.2.6 I/O Pin Output Characteristics of Middle Drive Capacity

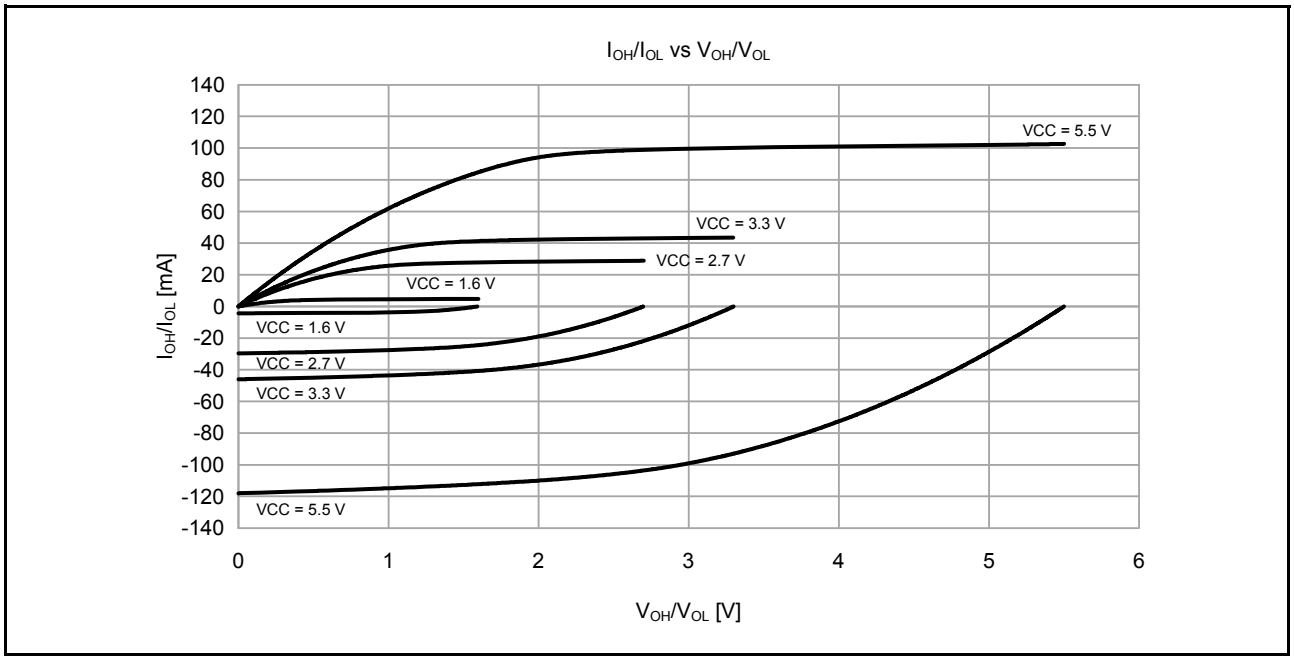


Figure 2.7 **V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at Ta = 25°C when middle drive output is selected (reference data)**

2.2.9 Operating and Standby Current

Table 2.11 Operating and standby current (1) (1 of 2)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter					Symbol	Typ*9	Max	Unit	Test Conditions
Supply current*1	High-speed mode*2	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 32 MHz	I_{CC}	3.6	-	mA	*7
				ICLK = 16 MHz		2.4	-		
				ICLK = 8 MHz		1.7	-		
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 32 MHz		5.6	-		
				ICLK = 16 MHz		3.5	-		
				ICLK = 8 MHz		2.4	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 32 MHz		9.5	-		*8
				ICLK = 16 MHz		5.4	-		
				ICLK = 8 MHz		3.3	-		
			All peripheral clock enabled, code executing from flash*5	ICLK = 32 MHz		-	21.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 32 MHz		1.5	-		*7
				ICLK = 16 MHz		1.1	-		
				ICLK = 8 MHz		0.9	-		
			All peripheral clock enabled*5	ICLK = 32 MHz		7.2	-		*8
				ICLK = 16 MHz		4.0	-		
				ICLK = 8 MHz		2.4	-		
		Increase during BGO operation*6				2.5	-		-
	Middle-speed mode*2	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 12 MHz	I_{CC}	1.7	-	mA	*7
				ICLK = 8 MHz		1.5	-		
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 12 MHz		2.7	-		
				ICLK = 8 MHz		1.9	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 12 MHz		3.9	-		*8
				ICLK = 8 MHz		3.0	-		
			All peripheral clock enabled, code executing from flash*5	ICLK = 12 MHz		-	8.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 12 MHz		0.8	-		*7
				ICLK = 8 MHz		0.8	-		
			All peripheral clock enabled*5	ICLK = 12 MHz		2.9	-		*8
				ICLK = 8 MHz		2.2	-		
		Increase during BGO operation*6				2.5	-		-
	Low-speed mode*3	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 1 MHz	I_{CC}	0.2	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 1 MHz		0.3	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 1 MHz		0.4	-		*8
			All peripheral clock enabled, code executing from flash*5	ICLK = 1 MHz		-	2.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 1 MHz		0.2	-		*7
			All peripheral clock enabled*5	ICLK = 1 MHz		0.3	-		*8

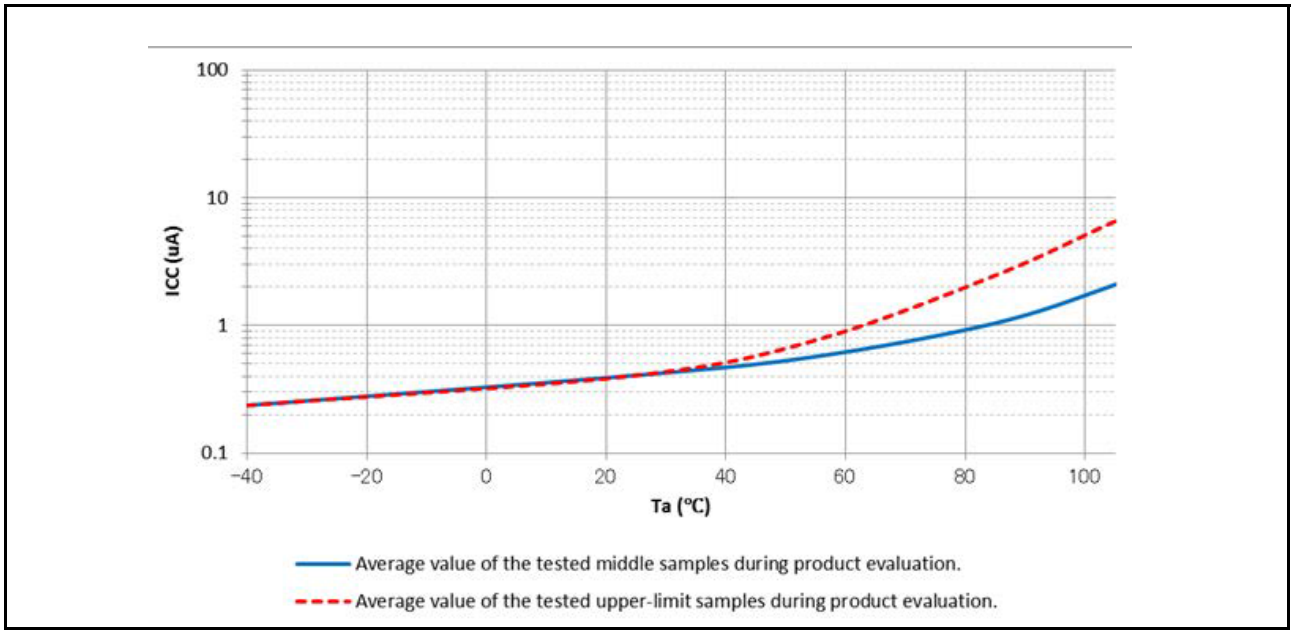


Figure 2.22 Temperature dependency in Software Standby mode (reference data)

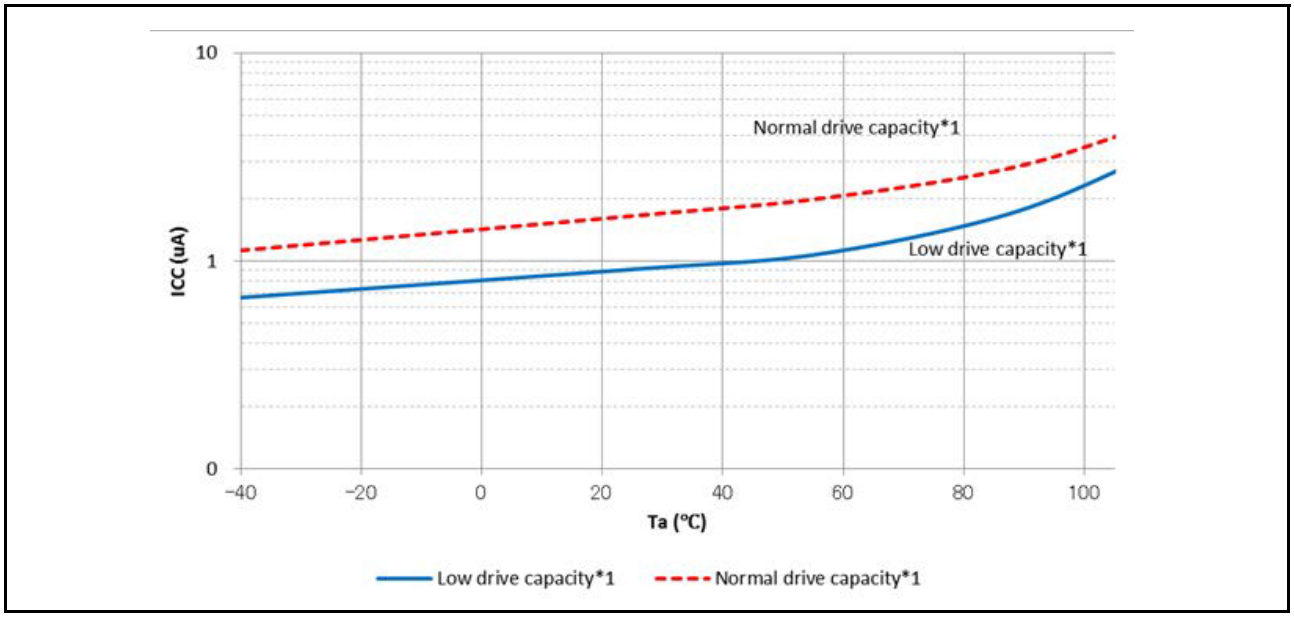


Figure 2.23 Temperature dependency of RTC operation (reference data)

Table 2.13 Operating and standby current (3) (1 of 2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Analog power supply current	During A/D conversion (at high-speed conversion)	I_{AVCC}	-	-	3.0	mA	-
	During A/D conversion (at low-power conversion)		-	-	1.0	mA	-
	During D/A conversion*1		-	0.4	0.8	mA	-
	Waiting for A/D and D/A conversion (all units)*5		-	-	1.0	µA	-
Reference power supply current	During A/D conversion	I_{REFH0}	-	-	150	µA	-
	Waiting for A/D conversion (all units)		-	-	60	nA	-
Temperature sensor		I_{TNS}	-	75	-	µA	-

Table 2.18 Operation frequency in low-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Typ	Max*5	Unit
Operation frequency	System clock (ICLK)*1, *2, *4	1.8 to 5.5 V	f	0.032768	-	1	MHz
	Peripheral module clock (PCLKB)*4	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKD)*3, *4	1.8 to 5.5 V		-	-	1	

Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory.
Note 2. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
Note 3. The lower-limit frequency of PCLKD is 1 MHz when the A/D converter is in use.
Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

Table 2.19 Operation frequency in low-voltage mode

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter			Symbol	Min	Typ	Max*5	Unit
Operation frequency	System clock (ICLK)*1, *2, *4	1.6 to 5.5 V	f	0.032768	-	4	MHz
	Peripheral module clock (PCLKB)*4	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKD)*3, *4	1.6 to 5.5 V		-	-	4	

Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory. When using ICLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
Note 2. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
Note 3. The lower-limit frequency of PCLKD is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

Table 2.20 Operation frequency in Subosc-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Typ	Max	Unit
Operation frequency	System clock (ICLK)*1, *3	1.8 to 5.5 V	f	27.8528	32.768	37.6832	kHz
	Peripheral module clock (PCLKB)*3	1.8 to 5.5 V		-	-	37.6832	
	Peripheral module clock (PCLKD)*2, *3	1.8 to 5.5 V		-	-	37.6832	

Note 1. Programming and erasing the flash memory is not possible.
Note 2. The 14-bit A/D converter cannot be used.
Note 3. See section 8, Clock Generation Circuit in User's Manual for the relationship between ICLK, PCLKB, and PCLKD frequencies.

Table 2.21 Clock timing (2 of 2)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Sub-clock oscillation stabilization time*2	t_{SUBOSC}	-	0.5	-	s	Figure 2.28

Note 1. Time until the clock can be used after the main clock oscillator stop bit (MOSCCR.MOSTP) is set to 0 (operating) when the external clock is stable.
Note 2. After changing the setting of the SOSCCR.SOSTP bit to start sub-clock oscillator operation, only start using the sub-clock oscillator after the sub-clock oscillation stabilization wait time elapsed. Use the oscillator wait time value recommended by the oscillator manufacturer.
Note 3. The 48-MHz HOCO can be used within a VCC range of 1.8 V to 5.5 V.
Note 4. The 64-MHz HOCO can be used within a VCC range of 2.4 V to 5.5 V.
Note 5. This is a characteristic when the HOCOCR.HCSTP bit is cleared to 0 (oscillation) in the MOCO stop state. When the HOCOCR.HCSTP bit is cleared to 0 (oscillation) during MOCO oscillation, this specification is shortened by 1 µs.
Note 6. Check OSCSF.HOCOSF to confirm whether stabilization time has elapsed.

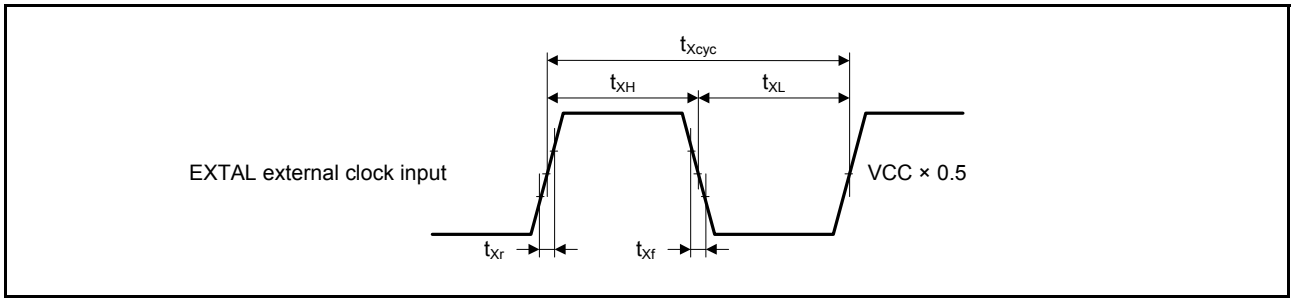


Figure 2.25 EXTAL external clock input timing

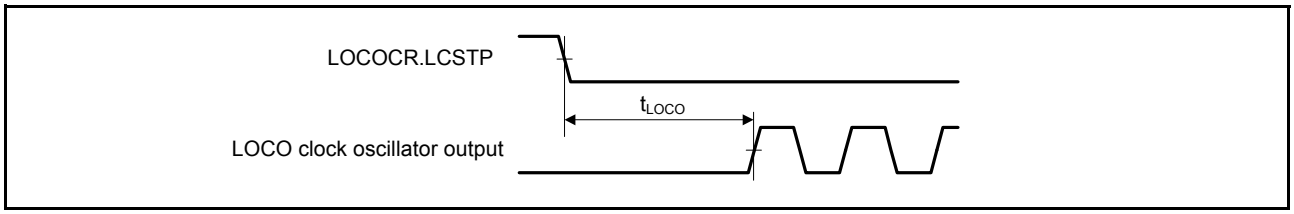


Figure 2.26 LOCO clock oscillation start timing

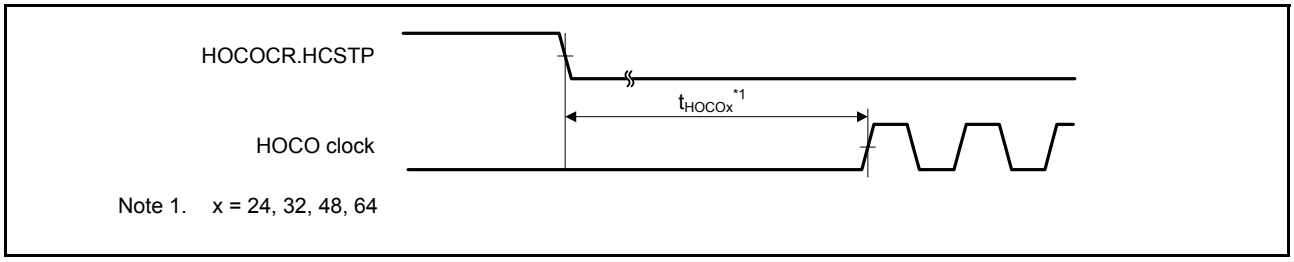


Figure 2.27 HOCO clock oscillation start timing (started by setting the HOCOCR.HCSTP bit)

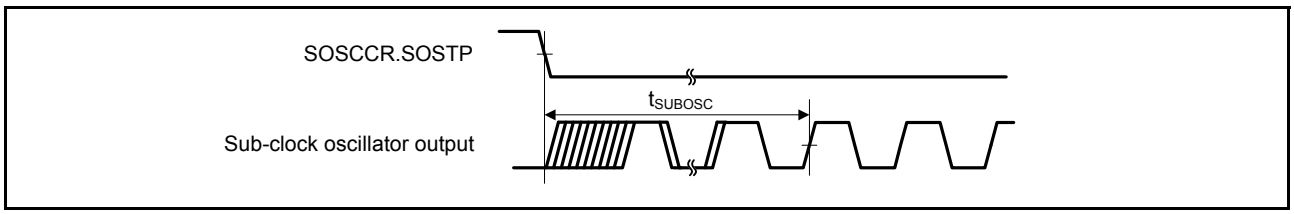


Figure 2.28 Sub-clock oscillation start timing

2.3.3 Reset Timing

Table 2.22 Reset timing

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
RES pulse width	At power-on	t_{RESWP}	3	-	-	ms	Figure 2.29
	Not at power-on	t_{RESW}	30	-	-	μs	Figure 2.30
Wait time after RES cancellation (at power-on)	LVD0 enabled*1	t_{RESWT}	-	0.7	-	ms	Figure 2.29
	LVD0 disabled*2		-	0.3	-		
Wait time after RES cancellation (during powered-on state)	LVD0 enabled*1	t_{RESWT2}	-	0.5	-	ms	Figure 2.30
	LVD0 disabled*2		-	0.05	-		
Internal reset cancellation time (Watchdog timer reset, SRAM parity error reset, Software reset)	LVD0 enabled*1	t_{RESWT3}	-	0.6	-	ms	
	LVD0 disabled*2		-	0.15	-		

Note 1. When OFS1.LVDAS = 0.
Note 2. When OFS1.LVDAS = 1.

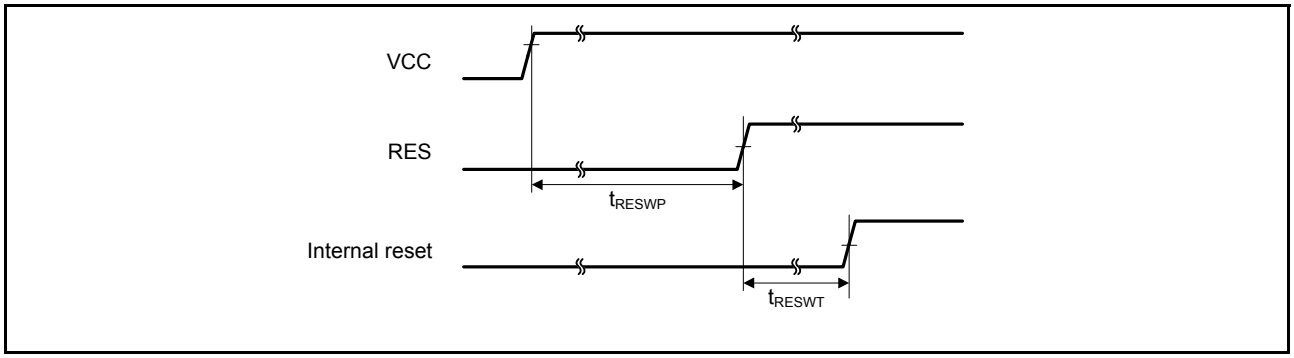


Figure 2.29 Reset input timing at power-on

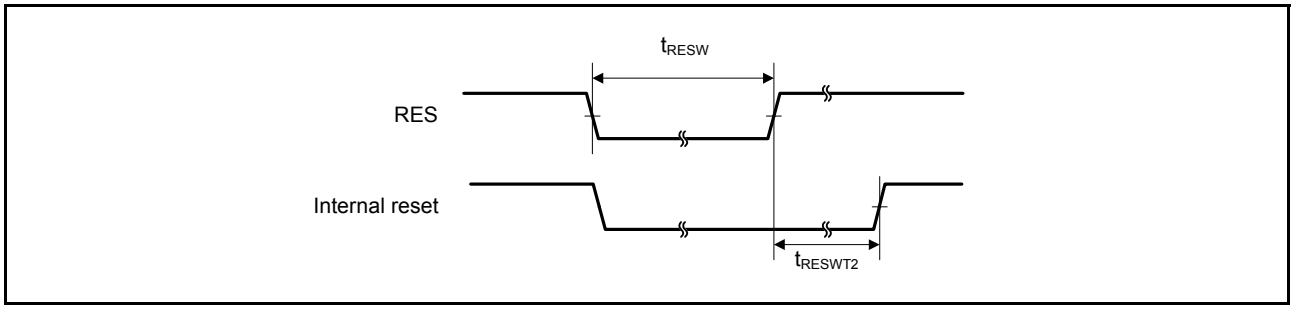


Figure 2.30 Reset input timing (1)

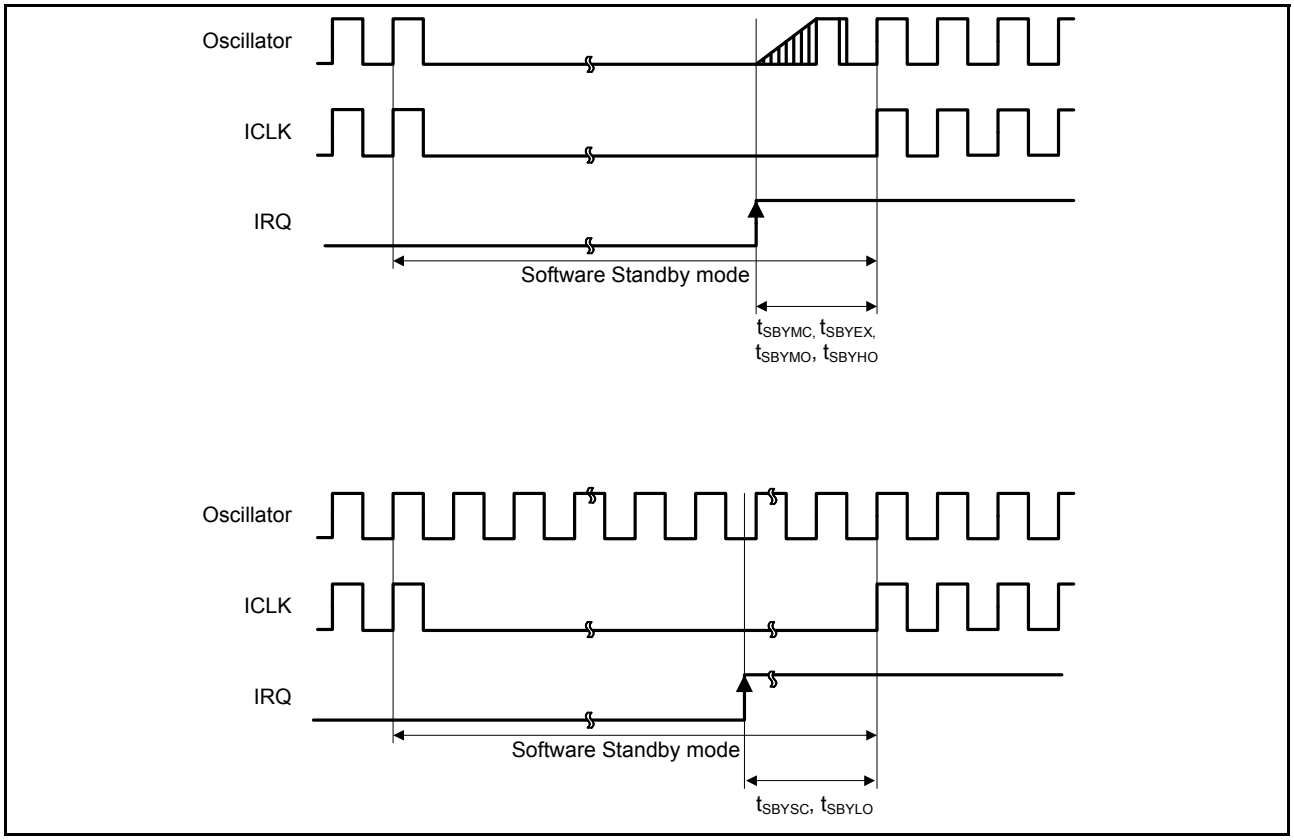
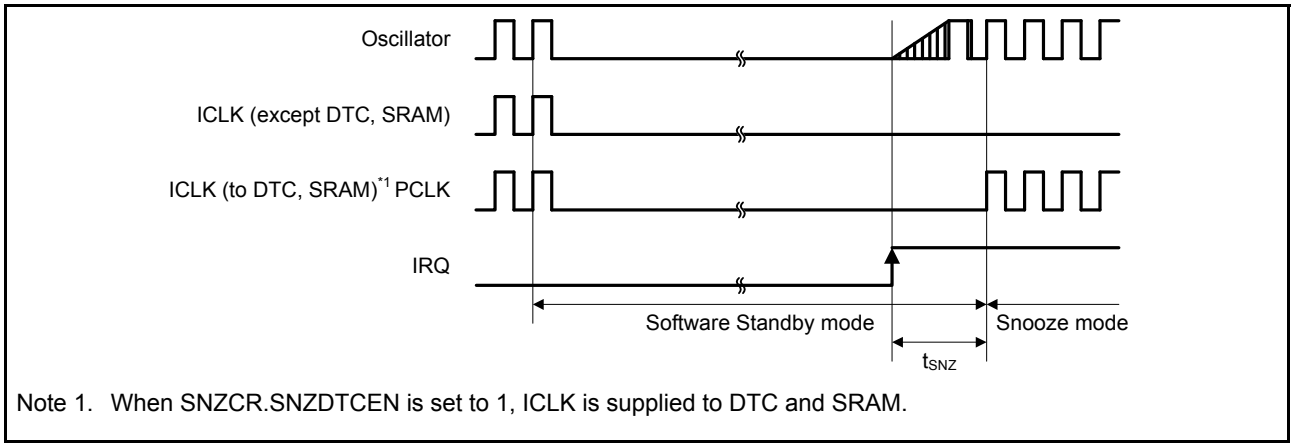


Figure 2.31 Software Standby mode cancellation timing

Table 2.28 Timing of recovery from low power modes (6)

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Recovery time from Software Standby mode to Snooze mode	High-speed mode System clock source is HOCO	t_{SNZ}	-	36	45	µs	Figure 2.32
	Middle-speed mode System clock source is MOCO	t_{SNZ}	-	1.3	3.6	µs	
	Low-speed mode System clock source is MOCO	t_{SNZ}	-	10	13	µs	
	Low-voltage mode System clock source is HOCO	t_{SNZ}	-	87	110	µs	



Note 1. When SNZCR.SNZDTCEN is set to 1, ICLK is supplied to DTC and SRAM.

Figure 2.32 Recovery timing from Software Standby mode to Snooze mode

2.3.5 NMI and IRQ Noise Filter

Table 2.29 NMI and IRQ noise filter

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
NMI pulse width	t_{NMIW}	200	-	-	ns	NMI digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2$*1	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-		NMI digital filter enabled	$t_{NMICK} \times 3 \leq 200$ ns
		$t_{NMICK} \times 3.5$*2	-	-			$t_{NMICK} \times 3 > 200$ ns
IRQ pulse width	t_{IRQW}	200	-	-	ns	IRQ digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2$*1	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-		IRQ digital filter enabled	$t_{IRQCK} \times 3 \leq 200$ ns
		$t_{IRQCK} \times 3.5$*3	-	-			$t_{IRQCK} \times 3 > 200$ ns

Note: 200 ns minimum in Software Standby mode.
Note 1. t_{Pcyc} indicates the PCLKB cycle.
Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock.
Note 3. t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock (i = 0 to 7).

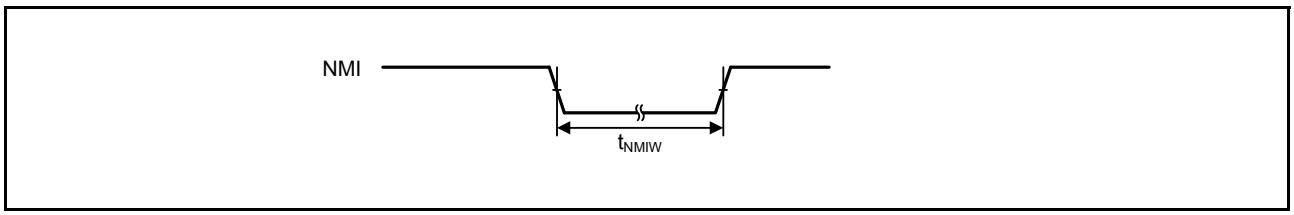


Figure 2.33 NMI interrupt input timing

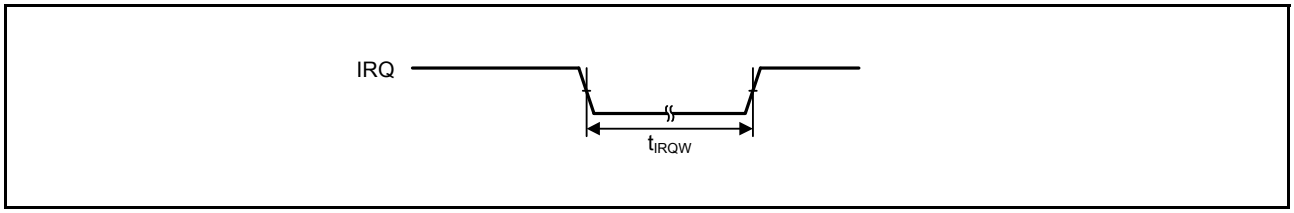


Figure 2.34 IRQ interrupt input timing

2.3.6 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 Trigger Timing

Table 2.30 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 trigger timing

Parameter			Symbol	Min	Max	Unit	Test conditions
I/O Ports	Input data pulse width		t_{PRW}	1.5	-	t_{Pcyc}	Figure 2.35
POEG	POEG input trigger pulse width		t_{POEW}	3	-	t_{Pcyc}	Figure 2.36
GPT	Input capture pulse width	Single edge	t_{GTICW}	1.5	-	t_{PDcyc}	Figure 2.37
		Dual edge		2.5	-		
AGT	AGTIO, AGTEE input cycle	2.7 V ≤ VCC ≤ 5.5 V	t_{ACYC}*1	250	-	ns	Figure 2.38
		2.4 V ≤ VCC < 2.7 V		500	-	ns	
		1.8 V ≤ VCC < 2.4 V		1000	-	ns	
		1.6 V ≤ VCC < 1.8 V		2000	-	ns	
	AGTIO, AGTEE input high level width, low-level width	2.7 V ≤ VCC ≤ 5.5 V	t_{ACKWH}, t_{ACKWL}	100	-	ns	
		2.4 V ≤ VCC < 2.7 V		200	-	ns	
		1.8 V ≤ VCC < 2.4 V		400	-	ns	
		1.6 V ≤ VCC < 1.8 V		800	-	ns	
	AGTIO, AGTO, AGTOA, AGTOB output cycle	2.7 V ≤ VCC ≤ 5.5 V	t_{ACYC2}	62.5	-	ns	Figure 2.38
		2.4 V ≤ VCC < 2.7 V		125	-	ns	
		1.8 V ≤ VCC < 2.4 V		250	-	ns	
		1.6 V ≤ VCC < 1.8 V		500	-	ns	
ADC14	14-bit A/D converter trigger input pulse width		t_{TRGW}	1.5	-	t_{Pcyc}	Figure 2.39
KINT	KRn (n = 00 to 07) pulse width		t_{KR}	250	-	ns	Figure 2.40

Note: tPcyc: PCLKB cycle, tPDcyc: PCLKD cycle.
Note 1. Constraints on AGTIO input: t_{Pcyc} × 2 (t_{Pcyc}: PCLKB cycle) < t_{ACYC}.

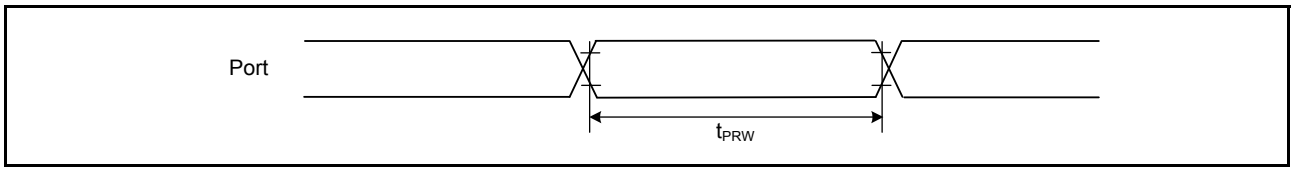


Figure 2.35 I/O ports input timing

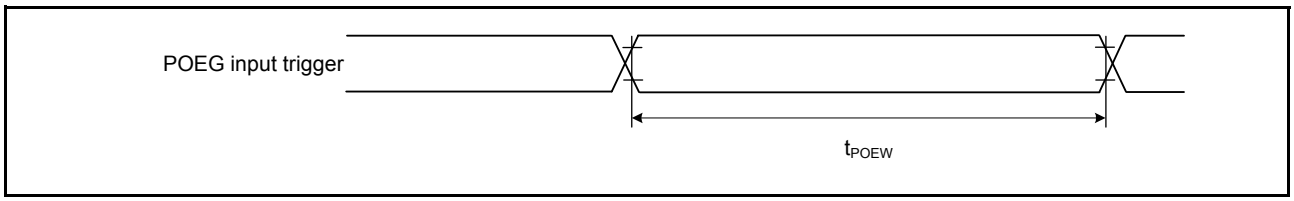


Figure 2.36 POEG input trigger timing

Note 2. t_{cac}: CAC count clock source cycle.

2.3.8 SCI Timing

Table 2.32 SCI timing (1)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter				Symbol	Min	Max	Unit*1	Test conditions
SCI	Input clock cycle	Asynchronous		t_{Scyc}	4	-	t_{Pcyc}	Figure 2.41
		Clock synchronous			6	-		
	Input clock pulse width			t_{SCKW}	0.4	0.6	t_{Scyc}	
	Input clock rise time			t_{SCKr}	-	20	ns	
	Input clock fall time			t_{SCKf}	-	20	ns	
	Output clock cycle	Asynchronous		t_{Scyc}	6	-	t_{Pcyc}	
		Clock synchronous			4	-		
	Output clock pulse width			t_{SCKW}	0.4	0.6	t_{Scyc}	
	Output clock rise time		1.8V or above	t_{SCKr}	-	20	ns	
			1.6V or above		-	30		
	Output clock fall time		1.8V or above	t_{SCKf}	-	20	ns	
			1.6V or above		-	30		
	Transmit data delay (master)	Clock synchronous	1.8V or above	t_{TXD}	-	40	ns	Figure 2.42
			1.6V or above		-	45		
	Transmit data delay (slave)	Clock synchronous	2.7V or above		-	55	ns	
			2.4V or above		-	60		
			1.8V or above		-	100		
			1.6V or above		-	125		
	Receive data setup time (master)	Clock synchronous	2.7V or above	t_{RXS}	45	-	ns	
			2.4V or above		55	-		
			1.8V or above		90	-		
			1.6V or above		110	-		
	Receive data setup time (slave)	Clock synchronous	2.7V or above		40	-	ns	
			1.6V or above		45	-		
	Receive data hold time (master)	Clock synchronous		t_{RXH}	5	-	ns	
	Receive data hold time (slave)	Clock synchronous		t_{RXH}	40	-	ns	

Note 1. t_{Pcyc}: PCLKB cycle.

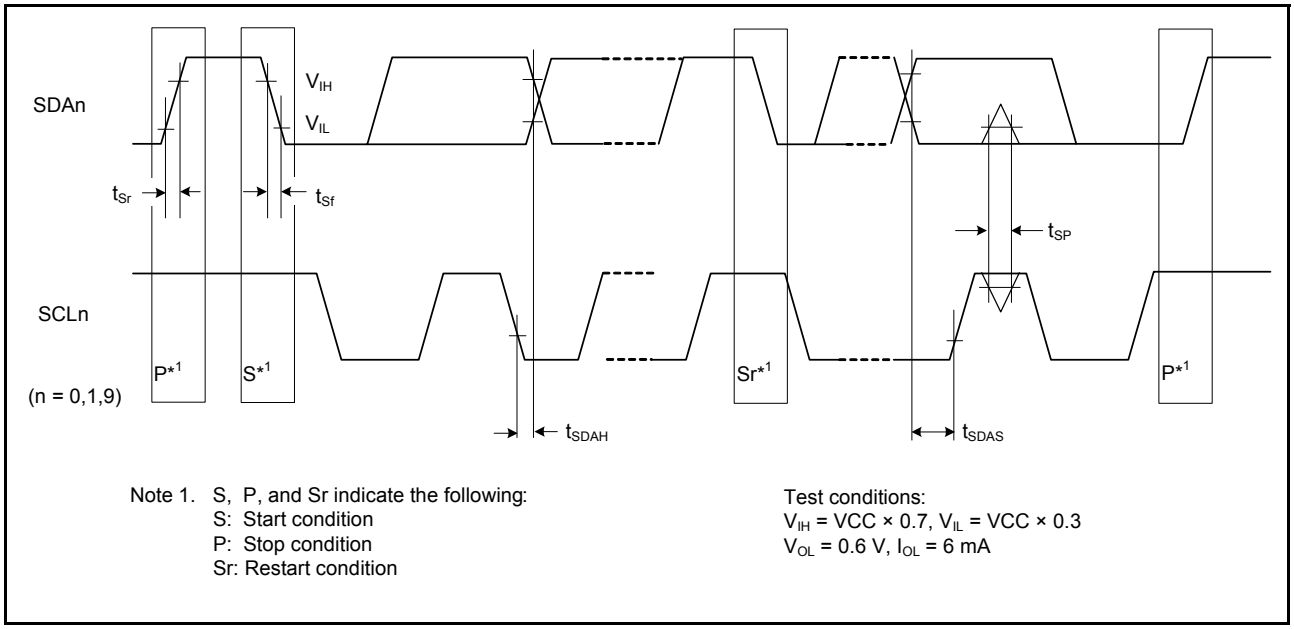


Figure 2.48 SCI simple IIC mode timing

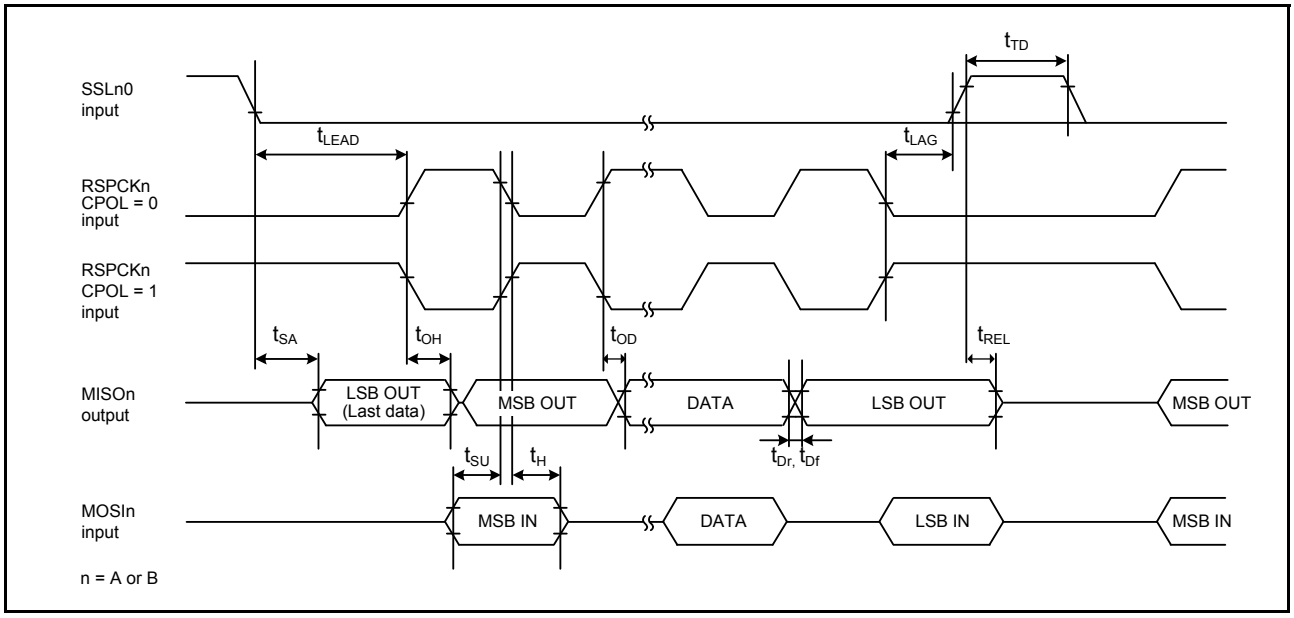


Figure 2.55 SPI timing (slave, CPHA = 1)

Table 2.40 A/D conversion characteristics (1) in high-speed A/D conversion mode (2 of 2)
Conditions: VCC = AVCC0 = 4.5 to 5.5 V, VREFH0 = 4.5 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Conversion time*1 (Operation at PCLKD = 64 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	0.80	-	-	µs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.22	-	-	µs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.
Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.
Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.
Note 3. Reference data.

Table 2.41 A/D conversion characteristics (2) in high-speed A/D conversion mode (1 of 2)
Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Frequency		1	-	48	MHz	-
Analog input capacitance*2	Cs	-	-	8*3	pF	High-precision channel
		-	-	9*3	pF	Normal-precision channel
Analog input resistance	Rs	-	-	2.5*3	kΩ	High-precision channel
		-	-	6.7*3	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-
Conversion time*1 (Operation at PCLKD = 48 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	0.94	-	-	µs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.50	-	-	µs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±0.5	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		-	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-

Table 2.46 A/D conversion characteristics (7) in low-power A/D conversion mode (2 of 2)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.6 to 5.5 V, VSS = AVSS0 = VREFL0 = 0
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter			Min	Typ	Max	Unit	Test Conditions
Analog input voltage range		Ain	0	-	VREFH0	V	-
12-bit mode							
Resolution			-	-	12	Bit	-
Conversion time*1 (Operation at PCLKD = 4 MHz)	Permissible signal source impedance Max. = 9.9 kΩ		13.5	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
			20.25	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error			-	±1.0	±7.5	LSB	High-precision channel
					±10.0	LSB	Other than above
Full-scale error			-	±1.5	±7.5	LSB	High-precision channel
					±10.0	LSB	Other than above
Quantization error			-	±0.5	-	LSB	-
Absolute accuracy			-	±3.0	±8.0	LSB	High-precision channel
					±12.0	LSB	Other than above
DNL differential nonlinearity error			-	±1.0	-	LSB	-
INL integral nonlinearity error			-	±1.0	±3.0	LSB	-
14-bit mode							
Resolution			-	-	14	Bit	-
Conversion time*1 (Operation at PCLKD = 4 MHz)	Permissible signal source impedance Max. = 9.9 kΩ		15.0	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
			21.75	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error			-	±4.0	±30.0	LSB	High-precision channel
					±40.0	LSB	Other than above
Full-scale error			-	±6.0	±30.0	LSB	High-precision channel
					±40.0	LSB	Other than above
Quantization error			-	±0.5	-	LSB	-
Absolute accuracy			-	±12.0	±32.0	LSB	High-precision channel
					±48.0	LSB	Other than above
DNL differential nonlinearity error			-	±4.0	-	LSB	-
INL integral nonlinearity error			-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.
Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.
Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.
Note 3. Reference data.

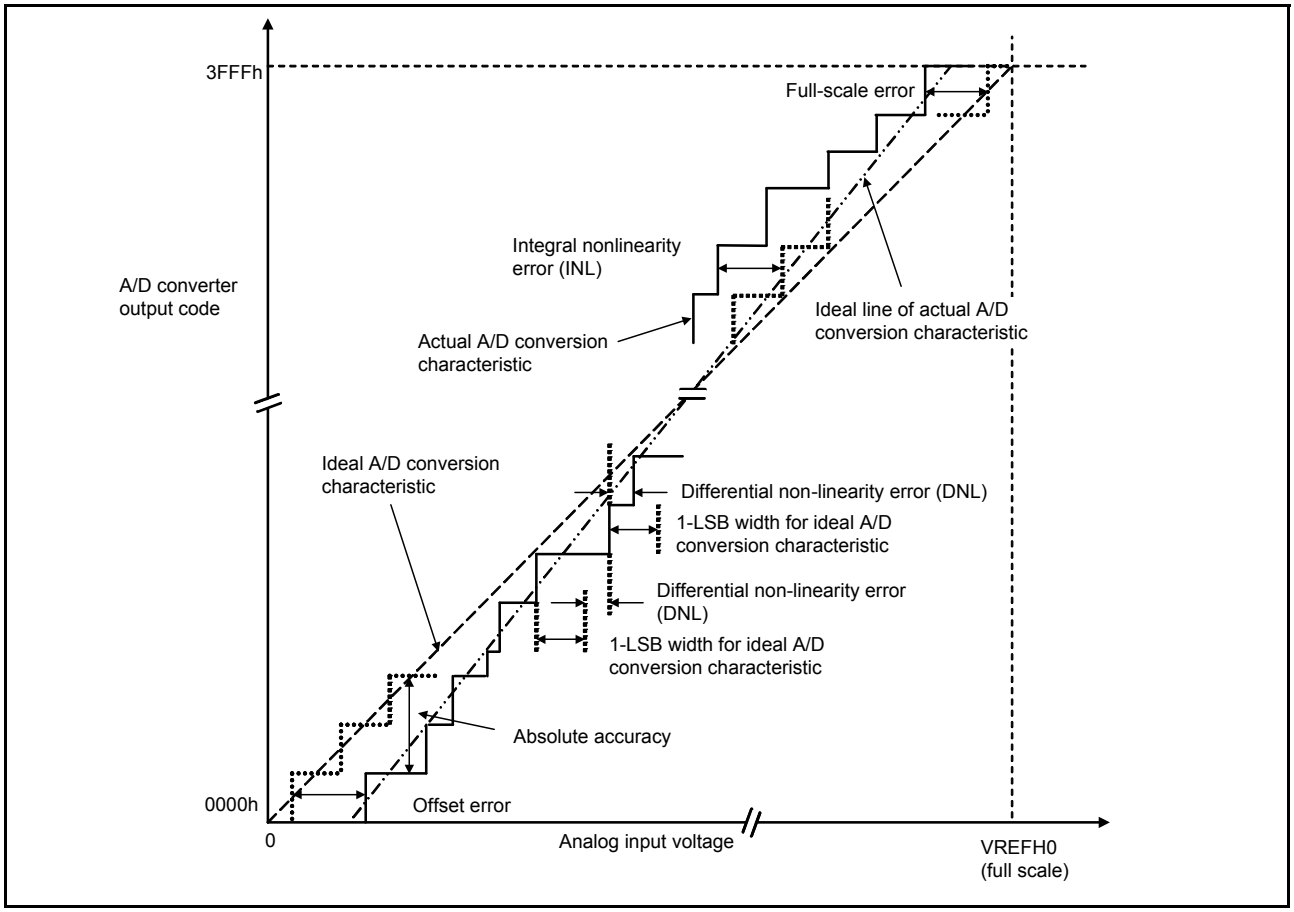


Figure 2.63 Illustration of 14-bit A/D converter characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of the analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as the analog input voltage. For example, if 12-bit resolution is used and the reference voltage VREFH0 = 3.072 V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If analog input voltage is 6 mV, an absolute accuracy of ±5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh, though an output code of 008h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

2.9 POR and LVD Characteristics

Table 2.52 Power-on reset circuit and voltage detection circuit characteristics (1)

Parameter		Symbol	Min	Typ	Max	Unit	Test Conditions
Voltage detection level*1	Power-on reset (POR)	V_{POR}	1.27	1.42	1.57	V	Figure 2.66, Figure 2.67
	Voltage detection circuit (LVD0)*2	V_{det0_0}	3.68	3.85	4.00	V	Figure 2.68 At falling edge VCC
		V_{det0_1}	2.68	2.85	2.96		
		V_{det0_2}	2.38	2.53	2.64		
		V_{det0_3}	1.78	1.90	2.02		
		V_{det0_4}	1.60	1.69	1.82		
	Voltage detection circuit (LVD1)*3	V_{det1_0}	4.13	4.29	4.45	V	Figure 2.69 At falling edge VCC
		V_{det1_1}	3.98	4.16	4.30		
		V_{det1_2}	3.86	4.03	4.18		
		V_{det1_3}	3.68	3.86	4.00		
		V_{det1_4}	2.98	3.10	3.22		
		V_{det1_5}	2.89	3.00	3.11		
		V_{det1_6}	2.79	2.90	3.01		
		V_{det1_7}	2.68	2.79	2.90		
		V_{det1_8}	2.58	2.68	2.78		
		V_{det1_9}	2.48	2.58	2.68		
		V_{det1_A}	2.38	2.48	2.58		
		V_{det1_B}	2.10	2.20	2.30		
		V_{det1_C}	1.84	1.96	2.05		
		V_{det1_D}	1.74	1.86	1.95		
		V_{det1_E}	1.63	1.75	1.84		
		V_{det1_F}	1.60	1.65	1.73		
	Voltage detection circuit (LVD2)*4	V_{det2_0}	4.11	4.31	4.48	V	Figure 2.70 At falling edge VCC
		V_{det2_1}	3.97	4.17	4.34		
		V_{det2_2}	3.83	4.03	4.20		
		V_{det2_3}	3.64	3.84	4.01		

Note 1. These characteristics apply when noise is not superimposed on the power supply. When a setting causes this voltage detection level to overlap with that of the voltage detection circuit, it cannot be specified whether LVD1 or LVD2 is used for voltage detection.

Note 2. # in the symbol $V_{det0\_\#}$ denotes the value of the OFS1.VDSEL1[2:0] bits.

Note 3. # in the symbol $V_{det1\_\#}$ denotes the value of the LVDLVLR.LVD1LVL[4:0] bits.

Note 4. # in the symbol $V_{det2\_\#}$ denotes the value of the LVDLVLR.LVD2LVL[2:0] bits.

Table 2.53 Power-on reset circuit and voltage detection circuit characteristics (2) (1 of 2)

Parameter		Symbol	Min	Typ	Max	Unit	Test Conditions
Wait time after power-on Reset cancellation	LVD0:enable	t_{POR}	-	1.7	-	ms	-
	LVD0:disable	t_{POR}	-	1.3	-	ms	-
Wait time after voltage monitor 0,1,2 reset cancellation	LVD0:enable*1	$t_{LVD0,1,2}$	-	0.6	-	ms	-
	LVD0:disable*2	$t_{LVD1,2}$	-	0.2	-	ms	-
Response delay*3		t_{det}	-	-	350	µs	Figure 2.66, Figure 2.67
Minimum VCC down time		t_{VOFF}	450	-	-	µs	Figure 2.66, VCC = 1.0 V or above

2.12 Flash Memory Characteristics

2.12.1 Code Flash Memory Characteristics

Table 2.56 Code flash characteristics (1)

Parameter		Symbol	Min	Typ	Max	Unit	Conditions
Reprogramming/erasure cycle*1		N_{PEC}	1000	-	-	Times	-
Data hold time	After 1000 times N_{PEC}	t_{DRP}	20*2, *3	-	-	Year	T_a = +85°C

Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 1,000), erasing can be performed n times for each block. For instance, when 4-byte programming is performed 256 times for different addresses in 1-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as 1. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited.)

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. This result is obtained from reliability testing.

Table 2.57 Code flash characteristics (2)

High-speed operating mode

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	ICLK = 1 MHz			ICLK = 32 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	4-byte	t_{P4}	-	116	998	-	54	506	µs
Erasure time	1-KB	t_{E1K}	-	9.03	287	-	5.67	222	ms
Blank check time	4-byte	t_{BC4}	-	-	56.8	-	-	16.6	µs
	1-KB	t_{BC1K}	-	-	1899	-	-	140	µs
Erase suspended time		t_{SED}	-	-	22.5	-	-	10.7	µs
Startup area switching setting time		t_{SAS}	-	21.9	585	-	12.1	447	ms
Access window time		t_{AWS}	-	21.9	585	-	12.1	447	ms
OCD/serial programmer ID setting time		t_{OSIS}	-	21.9	585	-	12.1	447	ms
Flash memory mode transition wait time 1		t_{DIS}	2	-	-	2	-	-	µs
Flash memory mode transition wait time 2		t_{MS}	5	-	-	5	-	-	µs

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.